

20V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	Max R _{DS(ON)}	Max I _D T _A = +25°C (Note 6)
20V	120mΩ @ $V_{GS} = 4.5V$	3.1A

Description and Applications

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

- DC DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

Features and Benefits

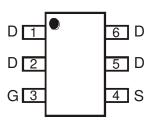
- Low On-resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

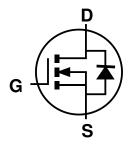
- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 3
- Weight: 0.016 grams (Approximate)







Pin-Out (Top View)



Equivalent Circuit

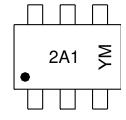
Ordering Information (Note 4)

Part Number	Marking	Reel Size (inch)	Tape Width (mm)	Quantity Per Reel
ZXMN2A01E6TA	2A1	7	8	3000
ZXMN2A01E6TC	2A1	13	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



2A1 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: C = 2015) M or \overline{M} = Month (ex: 9 = September)

Date Code Kev

Date Code Rey								
Year	2015	2016	2017	2018	2019	2020	2021	2022
Code	С	D	E	F	G	Н		J

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

	Characteristic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
		$T_A = +25^{\circ}C \text{ (Note 6)}$	I _D	3.1	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70^{\circ}C \text{ (Note 6)}$		2.5	Α
		$T_A = +25^{\circ}C \text{ (Note 5)}$		2.5	
Pulsed Drain Current (Note	7)		I _{DM}	11	Α
Continuous Source Current	(Body Diode) (N	lote 6)	I _S	2.4	Α
Pulsed Source Current (Bod	y Diode) (Note	7)	I _{SM}	11	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at T _A = +25°C (Note 5) Linear derating factor	P _D	1.1 8.8	W mW/°C
Power Dissipation at T _A = +25°C (Note 6) Linear Derating Factor	P _D	1.7 13.6	W mW/°C
Junction to Ambient (Note 5)	$R_{ hetaJA}$	113	°C/W
Junction to Ambient (Note 6)	$R_{ heta JA}$	70	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- 5. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions. 6. For a device surface mounted on FR-4 PCB measured at t ≤ 10 secs.
- 7. Repetitive rating 25mm x 25mm FR-4 PCB, D = 0.05, pulse width 10µs pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

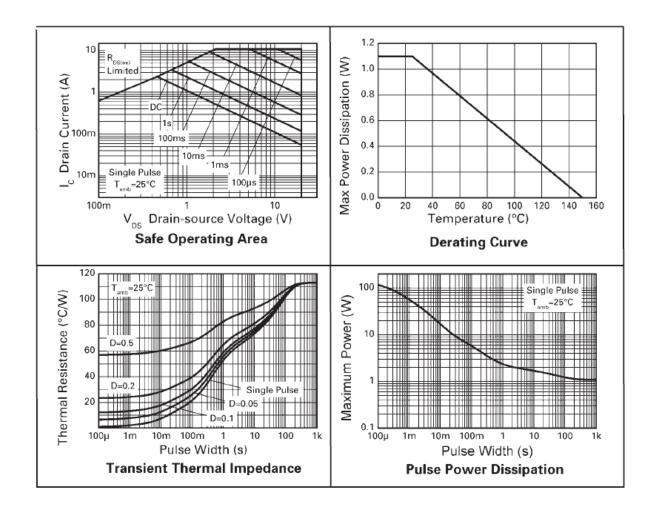
Characteristic		Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	20	-	-	V	$I_D = 250 \mu A, V_{GS} = 0 V$
Zero Gate Voltage Drain Current		-	-	1	μΑ	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Body Leakage	I _{GSS}	-	-	100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
Gate-Source Threshold Voltage	V _{GS(TH)}	0.7	-	-	٧	$I_D = 250 \mu A, V_{DS} = V_{GS}$
Static Drain-Source On-State Resistance (Note 8)			_	0.120	Ω	$V_{GS} = 4.5V, I_{D} = 4A$
Static Brain-Source On-State Hesistance (Note o)	R _{DS(ON)}		_	0.225	32	$V_{GS} = 2.5V, I_{D} = 1.5A$
Forward Transconductance (Notes 8 &10)	g _{fs}	-	6.1	-	S	$V_{DS} = 10V$, $I_D = 4A$
Diode Forward Voltage (Note 8)	V_{SD}	-	0.9	0.95	V	$T_J = +25^{\circ}C$, $I_S = 3.2A$, $V_{GS} = 0V$
DYNAMIC CHARACTERISTICS						
Input Capacitance (Note 10)	Ciss	-	303	-	pF	V 15V V 0V
Output Capacitance (Note 10)	Coss	-	59	-	pF	「V _{DS} = 15V, V _{GS} = 0V −f = 1MHz
Reverse Transfer Capacitance (Note 10)	C _{rss}	-	30	-	рF	1 – 1101112
Total Gate Charge (Notes 9 & 10)	Qg	-	3.0	-	nC	V 45V V 10V
Gate-Source Charge (Notes 9 & 10)	Q_{gs}	-	0.8	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V$ $I_{D} = 4A$
Gate-Drain Charge (Notes 9 & 10)	Q_{gd}	-	1.0	-	nC	ID = 4A
Turn-On Delay Time (Notes 9 & 10)	t _{D(ON)}	-	2.49	-	ns	
Turn-On Rise Time (Notes 9 & 10)	t _R	-	5.21	-	ns	$V_{DD} = 10V, V_{GS} = 5V$
Turn-Off Delay Time (Notes 9 & 10)	t _{D(OFF)}	-	7.47	-	ns	$I_D = 4A, R_G = 6.0\Omega$
Turn-Off Fall Time (Notes 9 & 10)	t_F	-	4.62	-	ns	
Reverse Recovery Time (Note 10)	t _{RR}	-	23	-	ns	$T_J = +25^{\circ}C, I_F=4A,$
Reverse Recovery Charge (Note 10)	Q_{RR}	-	5.65	-	nC	di/dt= 100A/µs

Notes: 8. Measured under pulsed conditions. Width=300 μ s. Duty cycle \leq 2%.

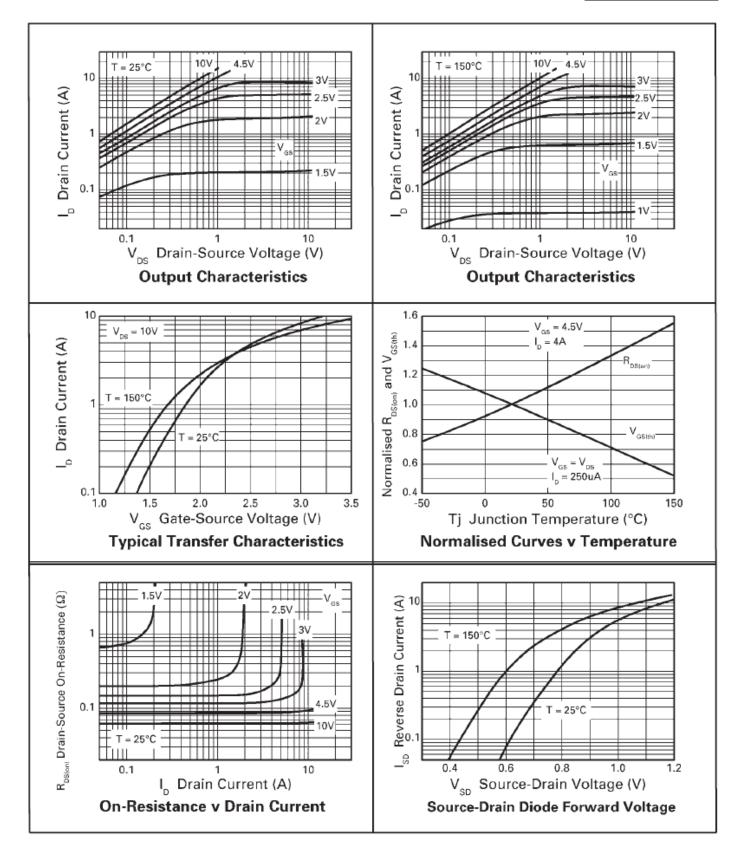
9. Switching characteristics are independent of operating junction temperature.

10. For design aid only, not subject to production testing.

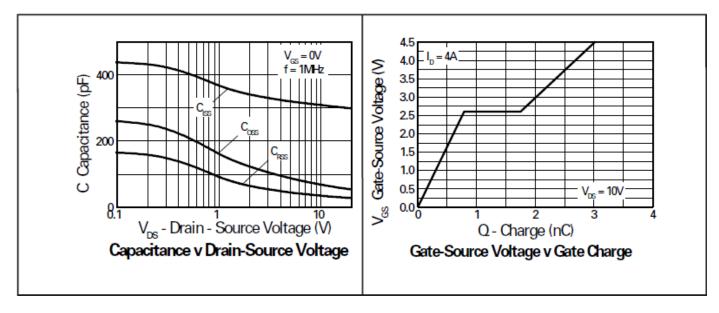


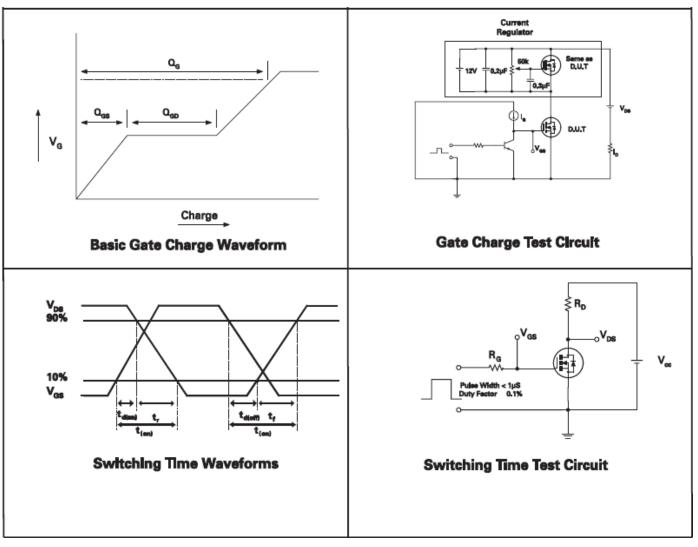








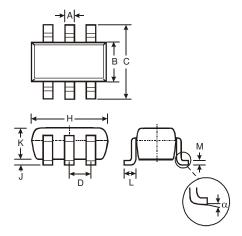






Package Outline Dimensions

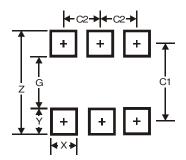
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT26						
Dim	Min	Max	Тур				
Α	0.35	0.50	0.38				
В	1.50	1.70	1.60				
O	2.70	3.00	2.80				
D	_	_	0.95				
Н	2.90	3.10	3.00				
J	0.013	0.10	0.05				
K	1.00	1.30	1.10				
L	0.35	0.55	0.40				
M	0.10	0.20	0.15				
α	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Υ	0.80
C1	2.40
C2	0.95



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